

**Preliminary Amendment**

Applicant: Thomas Hecht et al.

Serial No.: Unknown

(Priority Application No. DE 102 45 537.6)

(International Application No. PCT/DE03/03188)

Filed: Herewith

(Priority Date: September 30, 2002)

(International Filing Date: September 24, 2003)

Docket No.: I433.153.101/13.555

Title: METHOD AND PROCESS REACTOR FOR SEQUENTIAL GAS PHASE DEPOSITION BY MEANS OF A PROCESS CHAMBER AND AN AUXILIARY CHAMBER (As Amended)

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**IN THE ABSTRACT**

Please replace the Abstract with the following rewritten paragraph:

**Abstract**

**METHOD AND PROCESS REACTOR FOR SEQUENTIAL GAS PHASE  
DEPOSITION BY MEANS OF A PROCESS CHAMBER AND AN AUXILIARY  
CHAMBER**

**Abstract**

In a process chamber (10) of a process reactor (1), a sequential gas phase deposition (ALD, atomic layer deposition) of two or more precursors fed in by means of process gases is controlled. T, the process chamber (10) being is connected to an auxiliary chamber (20) for a change of precursor and so the precursor to be removed is rarefied in the process chamber (10), so that a process duration of the sequential gas phase deposition that is determined by a change of precursor is reduced.

(Figure 1)